

SILICON MULTIPLIER VARACTOR DIODE

DESCRIPTION:

The **1N4396** is a High Power Silicon Multiplier Varactor Diode.

MAXIMUM RATINGS

I_F	200 mA
V_R	250 V
P_{DISS}	20 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+150^\circ\text{C}$
T_{STG}	-65°C to $+175^\circ\text{C}$
θ_{JC}	5.0 $^\circ\text{C/W}$

PACKAGE STYLE DO-4				
SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A		0.405		10.28
b		0.250		6.35
c				
ϕD		0.505		12.82
ϕD_1	0.265	0.424	6.74	10.76
E	0.423	0.438	10.75	11.12
F_1	0.075	0.175	1.91	4.44
J	0.600	0.800	15.24	20.32
ϕM	0.163	0.189	4.15	4.80
N	0.422	0.453	10.72	11.50
N_1		0.078		1.98
S				
ϕT	0.060	0.095	1.53	2.41
ϕW	10-32	UNF-2A	10-32	UNF-2A

1 = Anode
2 = Cathode

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{BR}	$I_R = 10 \mu\text{A}$	250			V
C_T	$V_R = 6.0 \text{ V}$ $f = 1.0 \text{ MHz}$	20		50	pF
R_S	$V_R = 6.0 \text{ V}$ $f = 50 \text{ MHz}$		0.7		Ohms
$P_{OUT(X3)}$	$P_{IN} = 30 \text{ W}$ $F_{IN} = 150 \text{ MHz}$	15			W